# 2SC4628

#### Silicon NPN Planar

# **HITACHI**

ADE-208-1114 (Z) 1st. Edition Mar. 2001

## Application

High frequency amplifier

#### Outline

TO-92 (2)

1. Emitter
2. Collector
3. Base



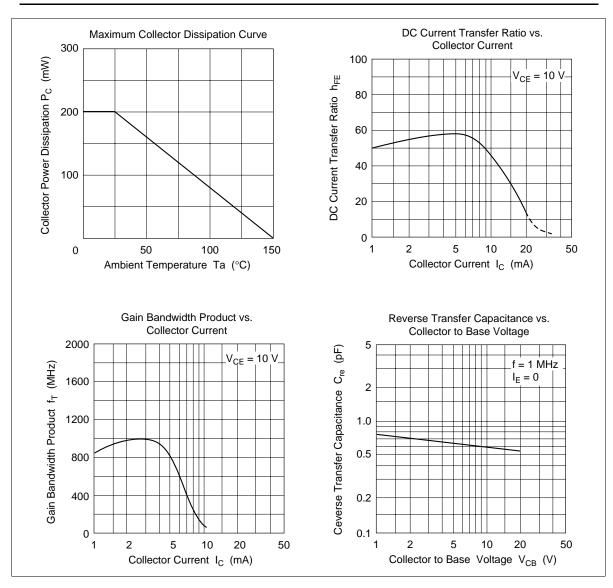
## 2SC4628

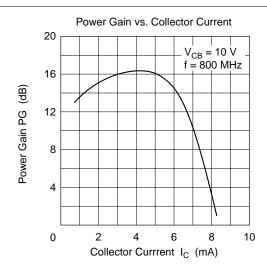
## **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

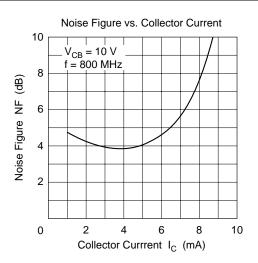
Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	20	V
Collector to emitter voltage	V <sub>CEO</sub>	20	V
Emitter to base voltage	V <sub>EBO</sub>	3	V
Collector current	I <sub>c</sub>	20	mA
Collector power dissipation	P <sub>c</sub>	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

## Electrical Characteristics ( $Ta = 25^{\circ}C$ )

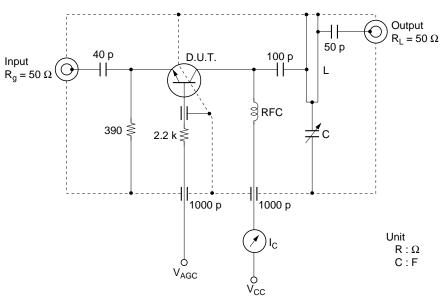
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	_	_	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter cutoff current	I <sub>EBO</sub>	_	_	10	μΑ	$V_{EB} = 3 \text{ V}, I_{C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	1	μΑ	V <sub>CB</sub> = 15 V, I <sub>E</sub> = 0
DC current transfer ratio	h <sub>FE</sub>	60	_	320		$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$
Gain bandwidth product	f <sub>T</sub>	600	_	_	MHz	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$
Reverse transfer capacitance	Cre	_	_	0.9	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0,$ emitter common, f = 1  MHz
Power gain	PG	10	_	_	dB	$V_{CB} = 10 \text{ V}, I_{C} = 2 \text{ mA},$ f = 800 MHz
Noise figure	NF	_	_	7.0	dB	







#### 800 MHz Power Gain and Noise Figure Test Circuit

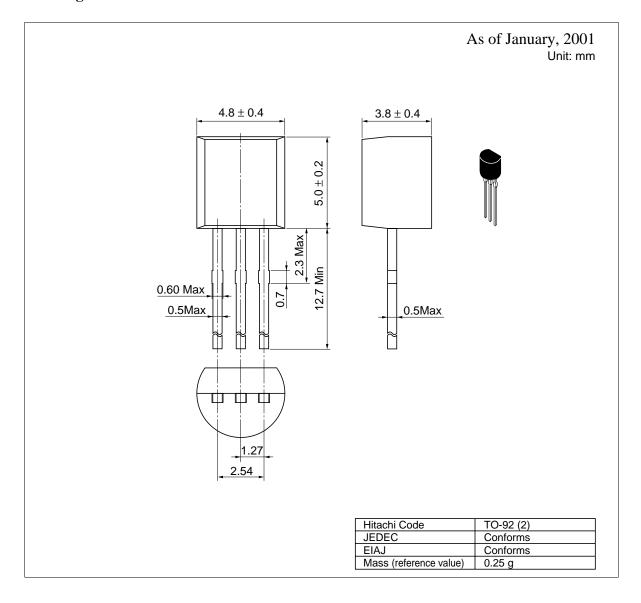


C : 0.5 to 10 pF variable capacitance L :  $\lambda/4$  silver platede copper  $26 \times 3 \times 1$  (mm) Collector tap to ground distance: 7 mm Output tap to ground distance: 3 mm

RFC : 0.17 mm copper wire, 2.4 mm inside dia, 16 turns

-3 dB down bandwidth is 40 MHz

#### **Package Dimensions**



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